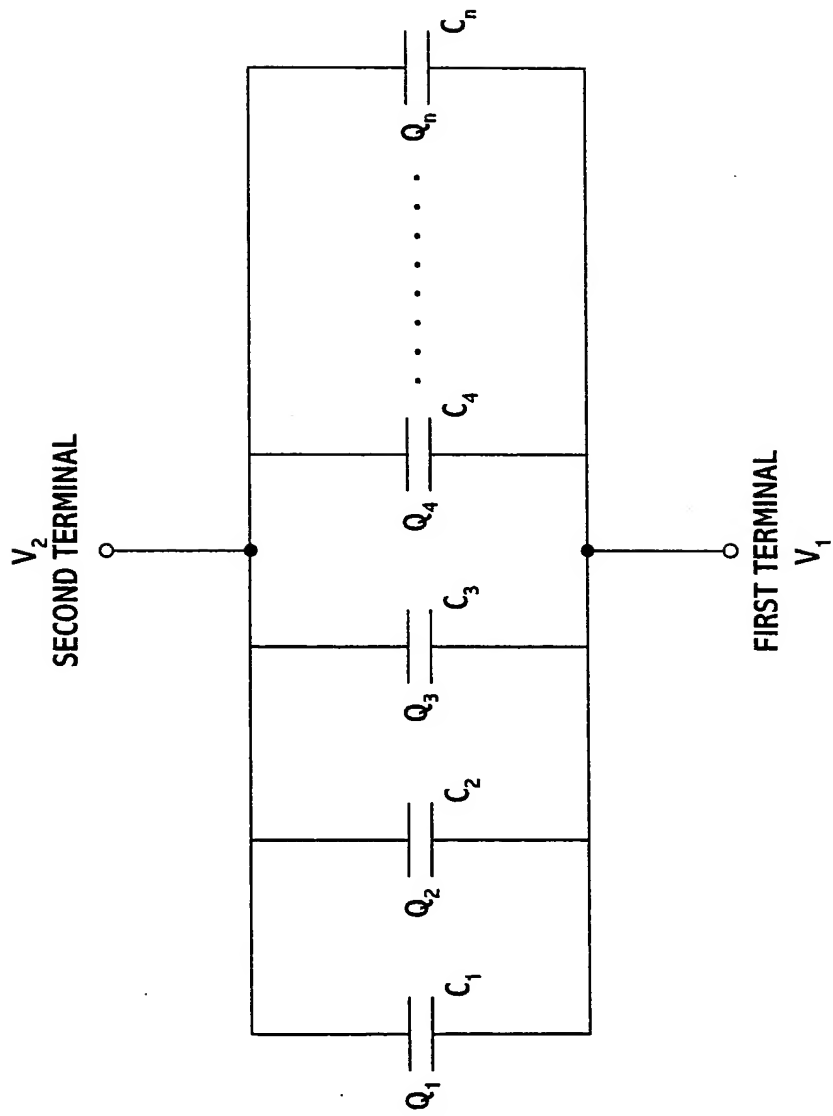


$$Q_{\text{TOTAL}} = Q_1 + Q_2 + Q_3 + Q_4 + Q_5 + Q_6 + Q_7 + Q_8 + Q_9 + Q_{10} + Q_{11}$$



$$Q = CV$$

$$C_{\text{TOTAL}} = C_1 + C_2 + C_3 + \dots + C_n$$

$$\Delta V = V_2 - V_1$$

FIG. 3

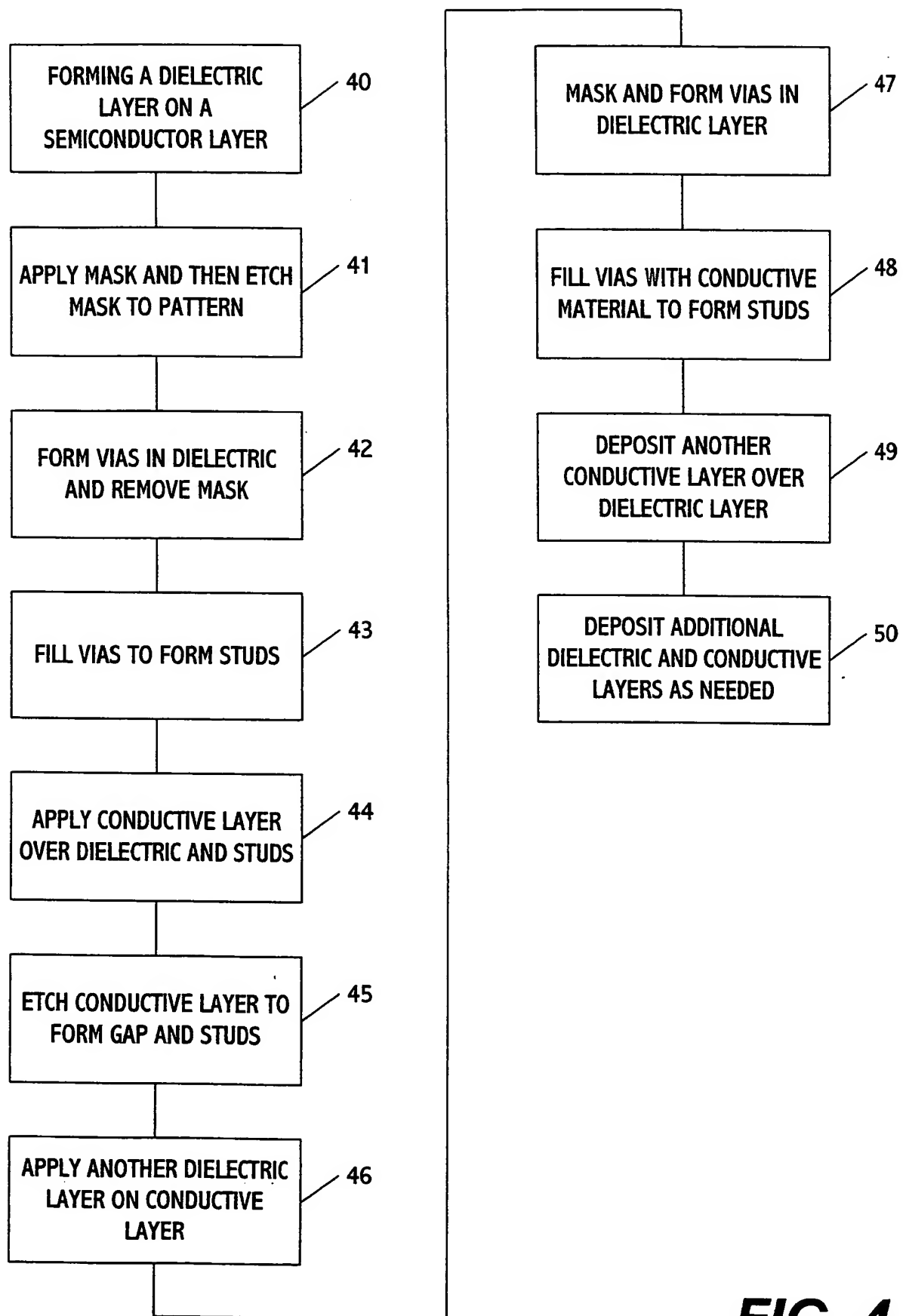


FIG. 4

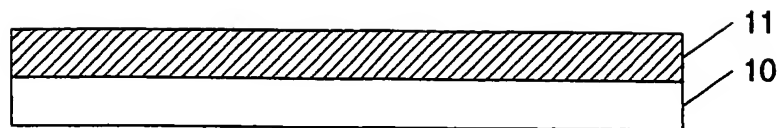


FIG. 5(a)

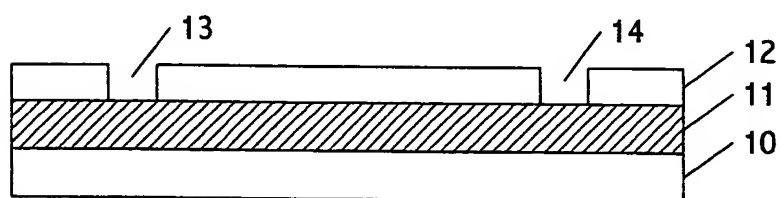


FIG. 5(b)

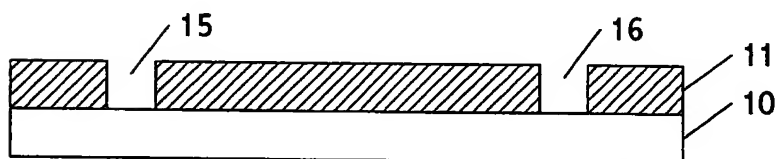


FIG. 5(c)

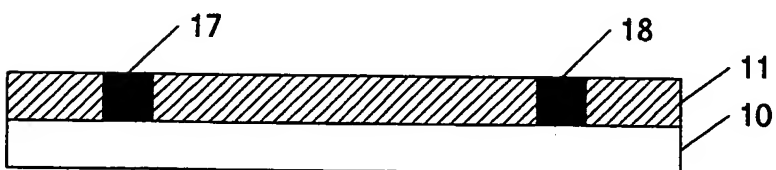


FIG. 5(d)

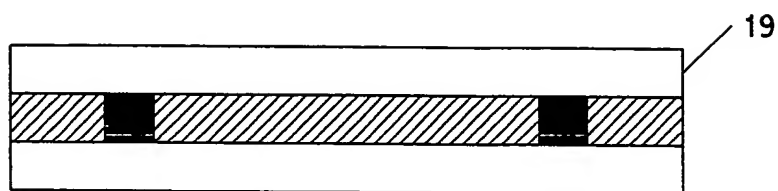


FIG. 5(e)

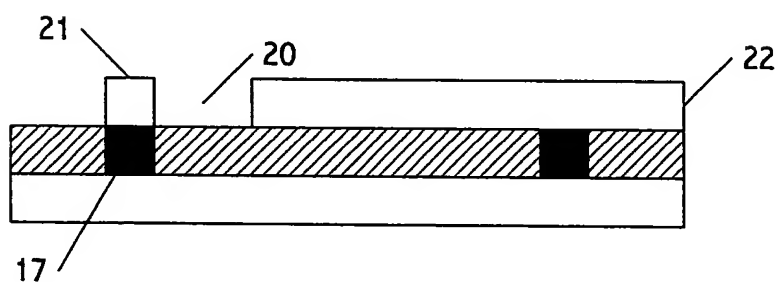


FIG. 5(f)

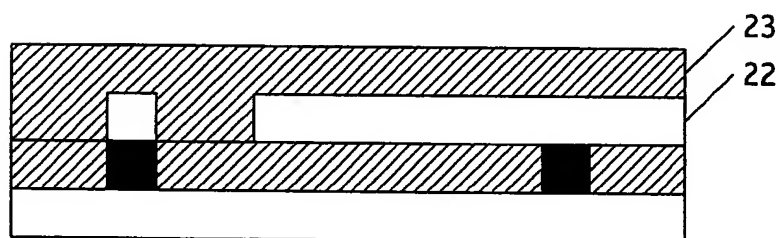


FIG. 5(g)

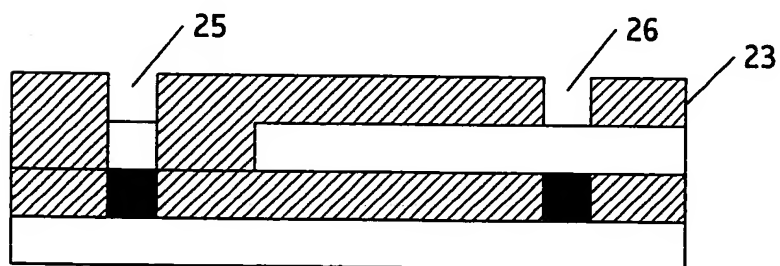


FIG. 5(h)

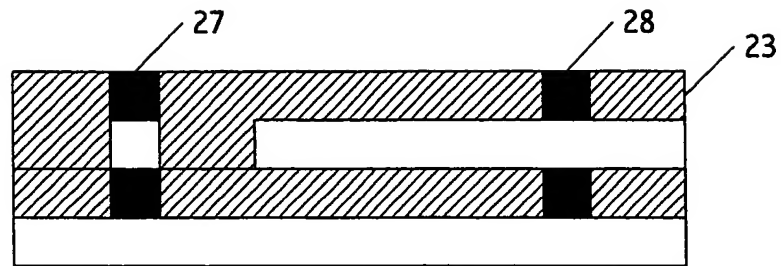


FIG. 5(i)

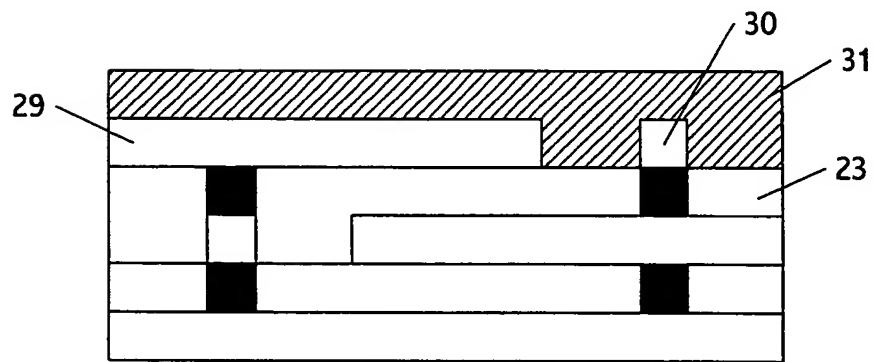


FIG. 5(j)

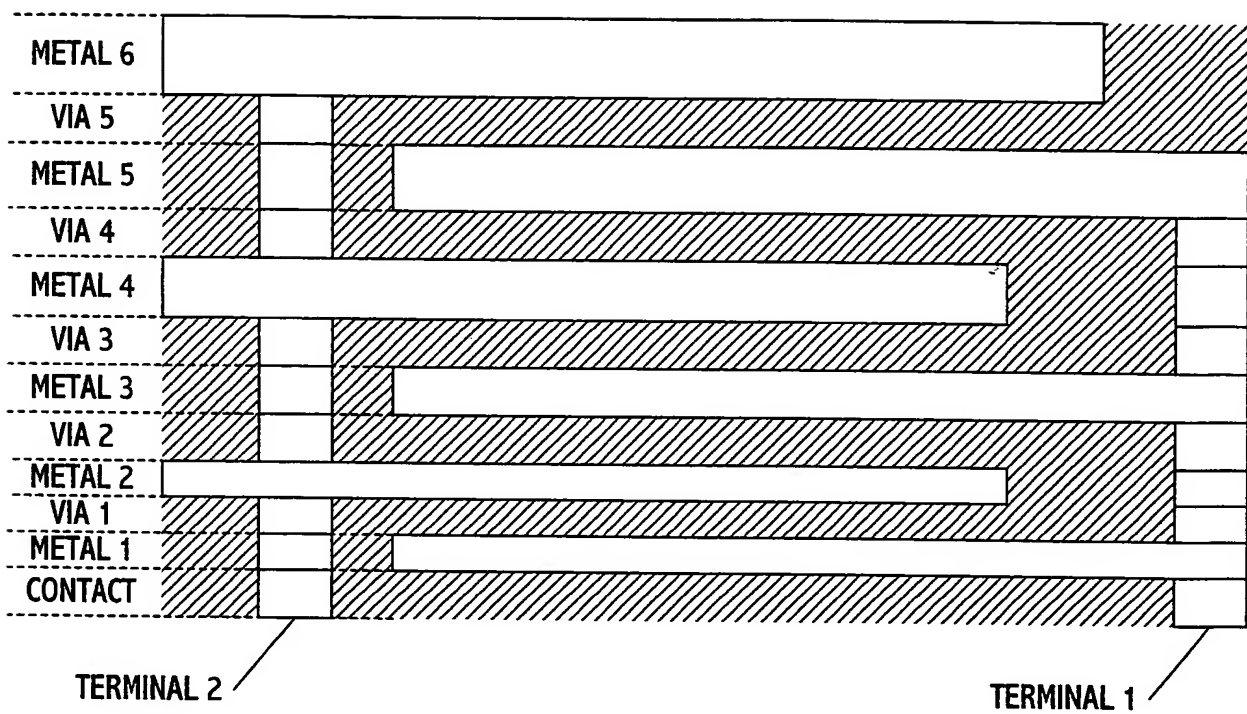


FIG. 5(k)

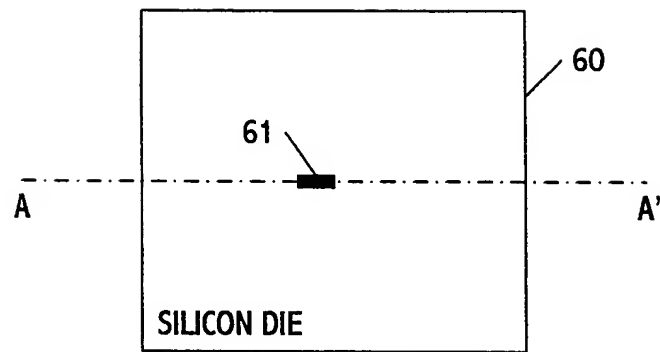


FIG. 6(a)

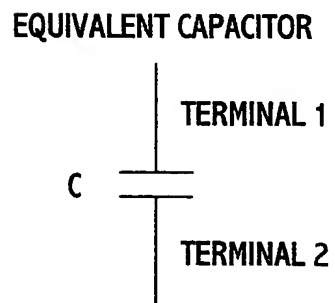


FIG. 6(b)

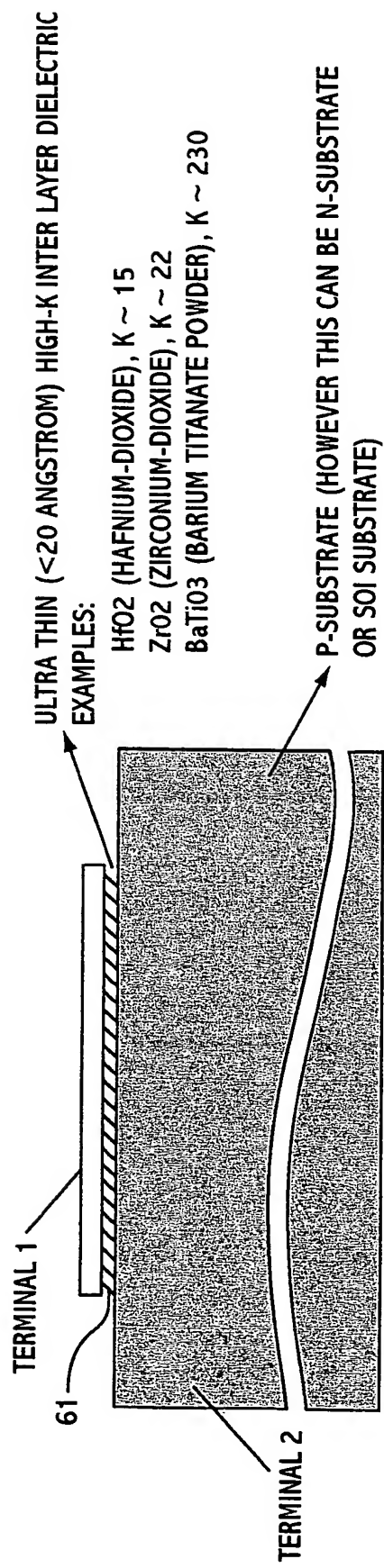


FIG. 6(c)

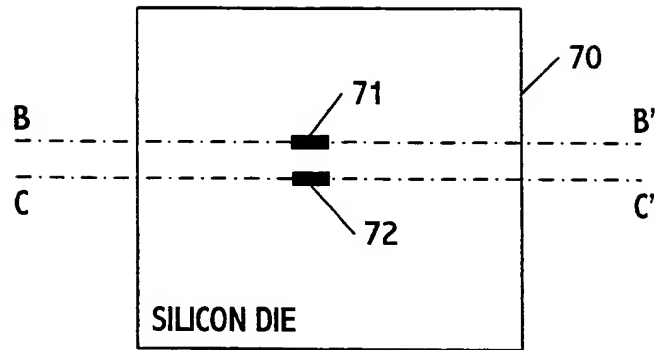


FIG. 7(a)

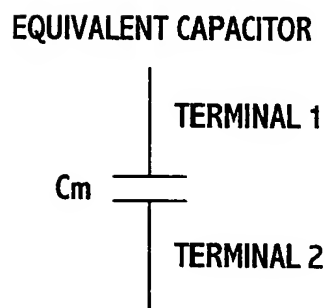


FIG. 7(b)

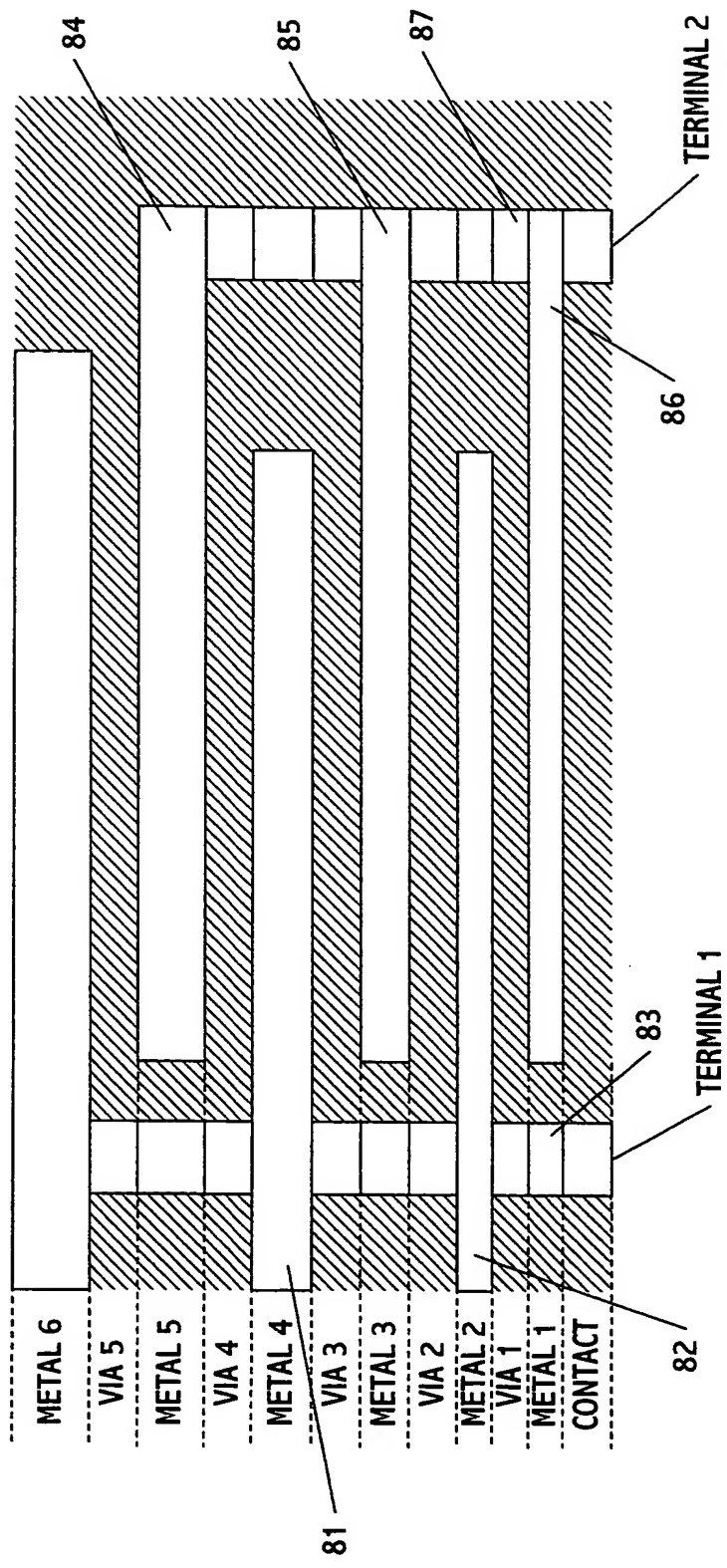


FIG. 8(a)

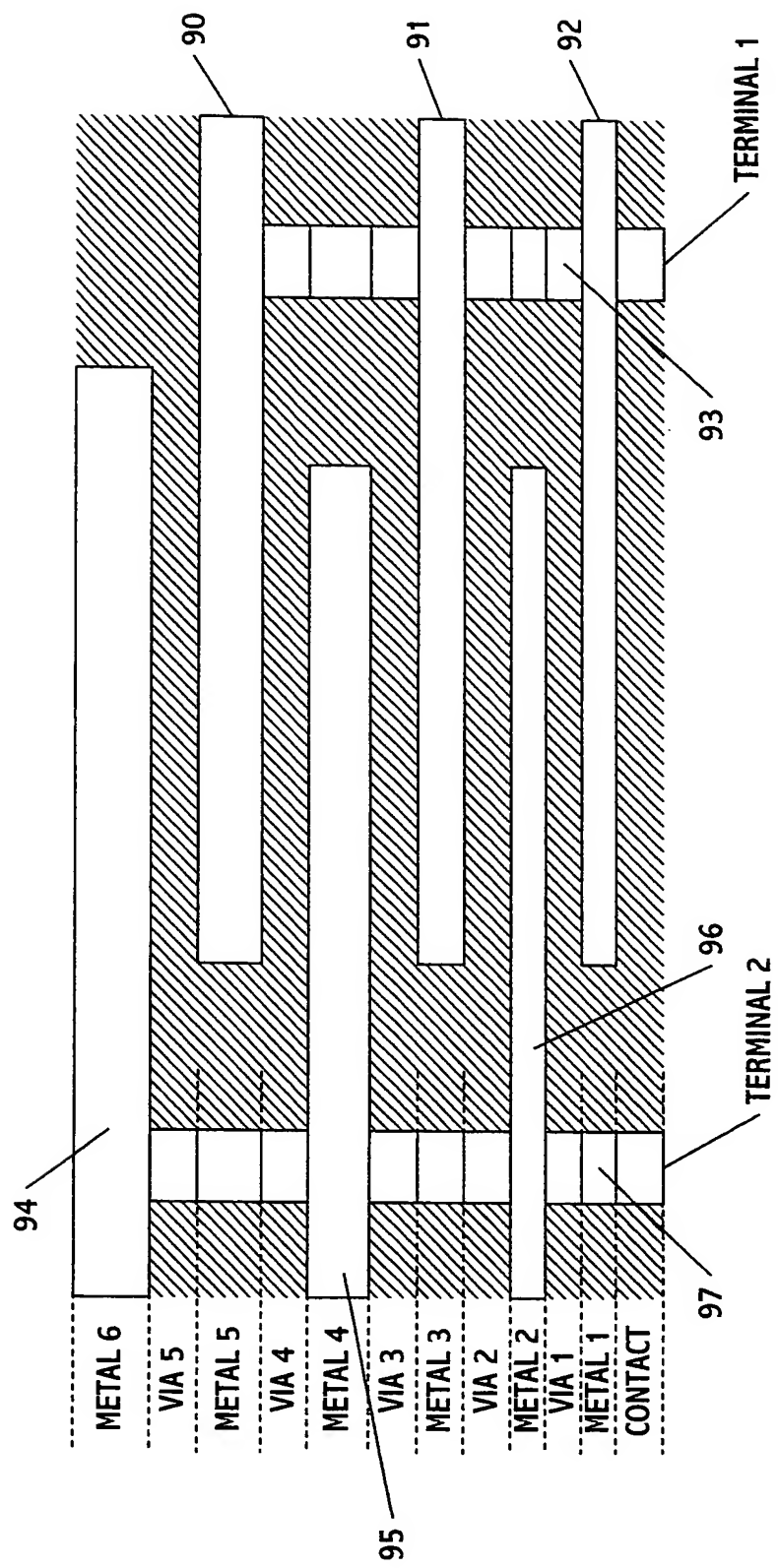


FIG. 8(b)

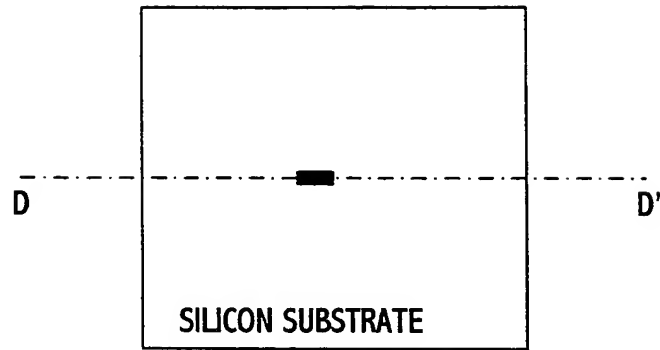


FIG. 9(a)

EQUIVALENT CAPACITOR

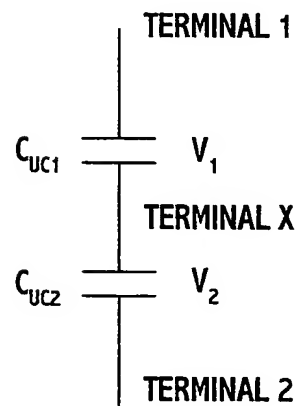


FIG. 9(b)

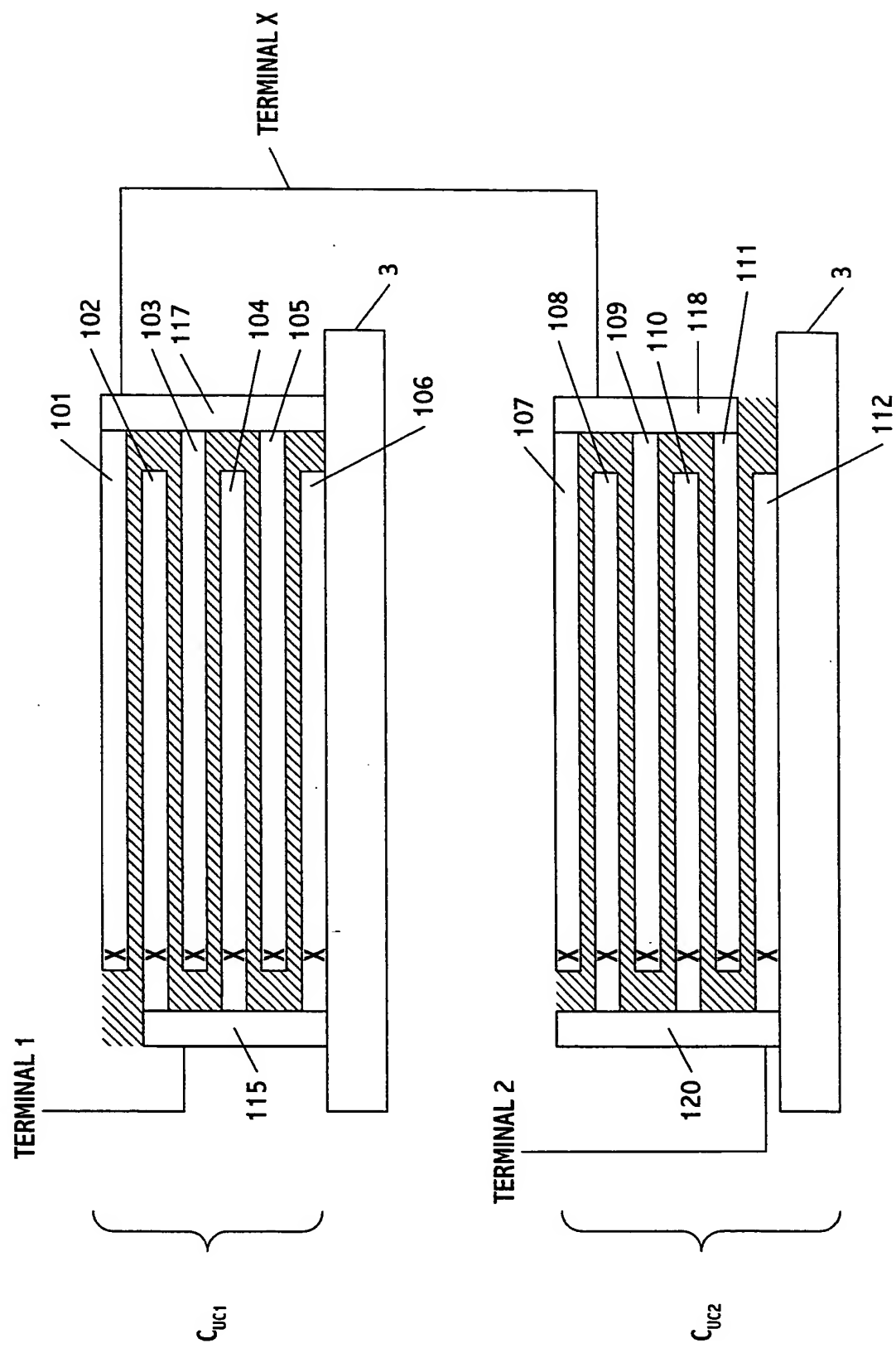
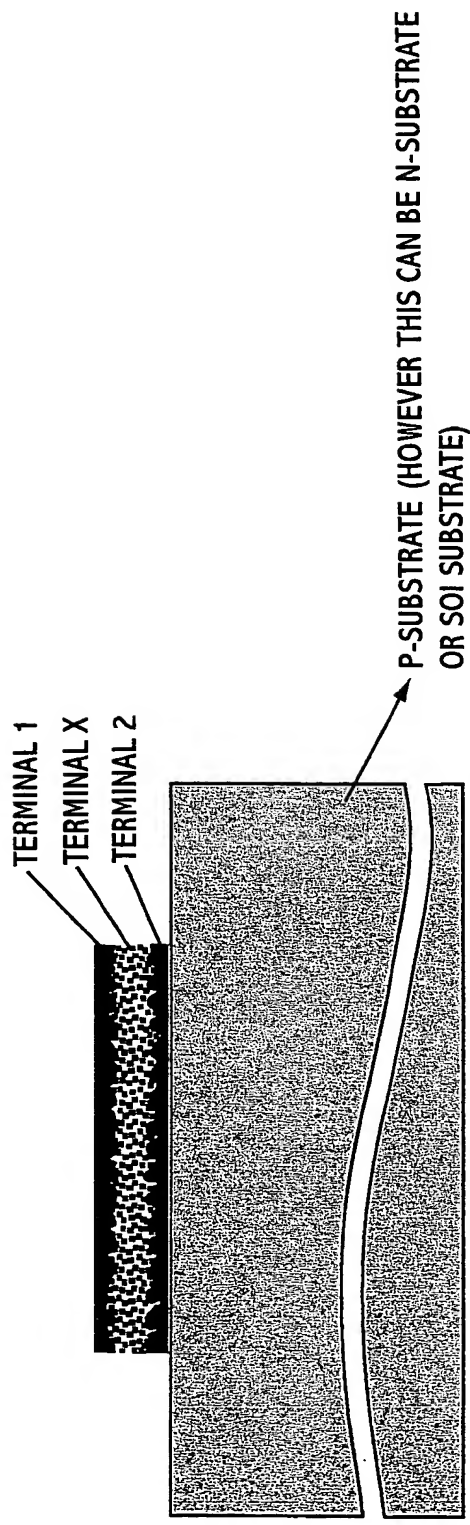


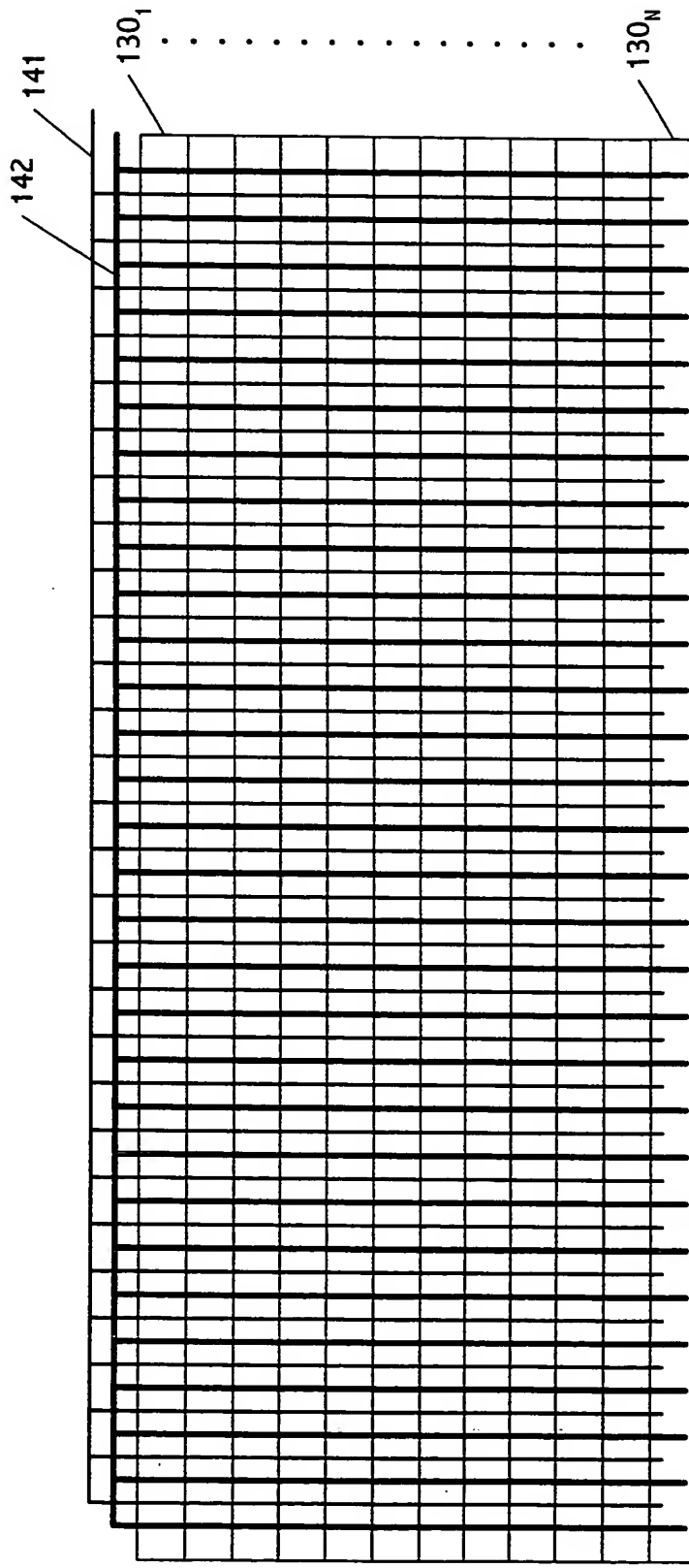
FIG. 10



ELECTRODE (TERMINAL 1) - EXAMPLE: POROUS CARBON OR DOPED SILICON. CAN BE CONDUCTIVE CARBON OR SILICON NANOTUBE
 ELECTROLYTE (TERMINAL X) - EXAMPLE: POTASSIUM HYDROXIDE
 ELECTRODE (TERMINAL 2) - EXAMPLE: POROUS CARBON OR DOPED SILICON. CAN BE CONDUCTIVE CARBON OR SILICON NANOTUBE

FIG. 11

EXAMPLE CROSS SECTION SHOWING STACKING OF MULTIPLE
SUBSTRATE TO INCREASE THE CAPACITANCE PER UNIT AREA



— TERMINAL 1
— TERMINAL 2

FIG. 12

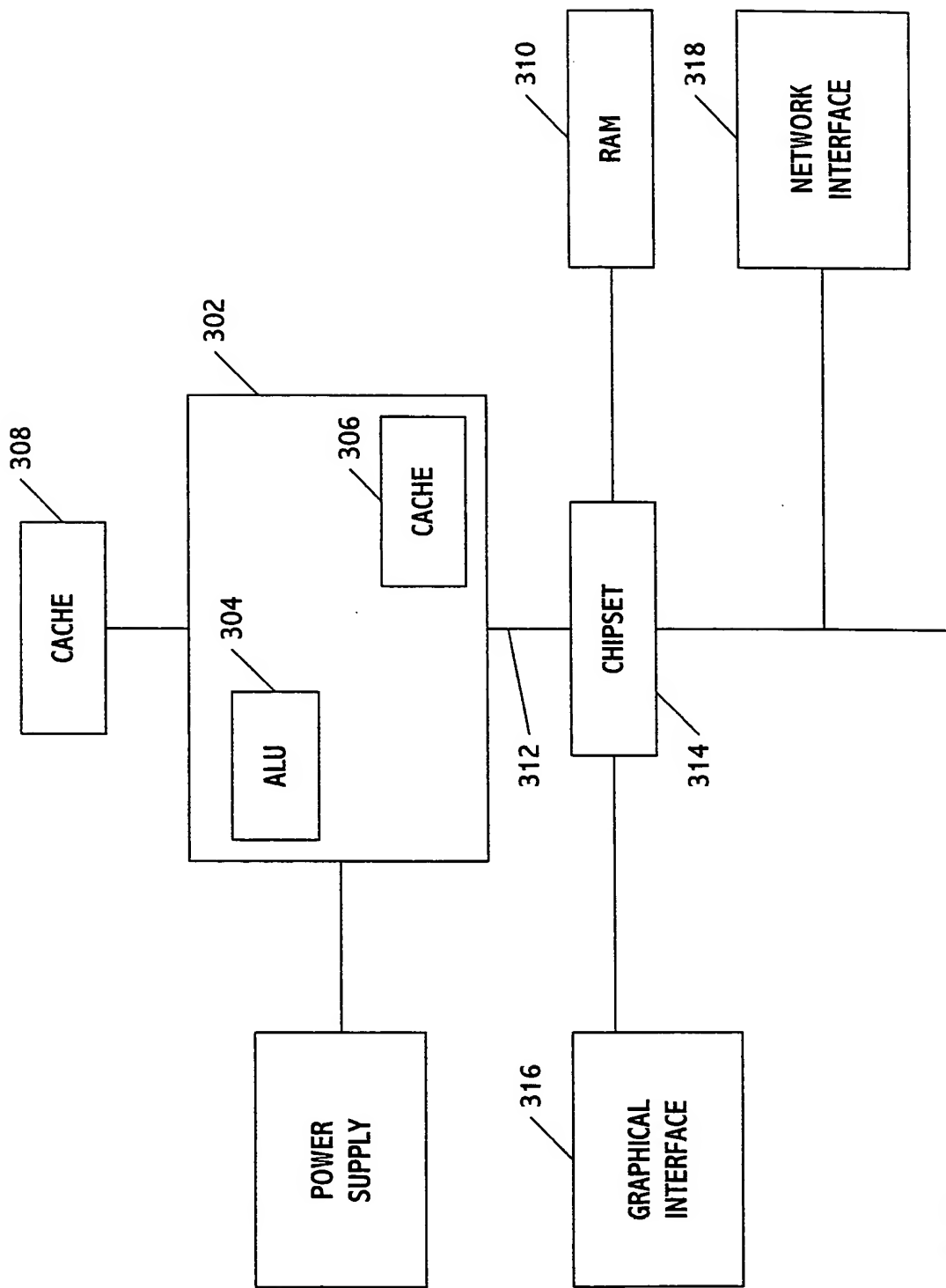


FIG. 13